

IN THE CLAIMS

This listing of claims will replace all previous versions and listings of claims in the application:

LISTING OF CLAIMS

Claims 1-19 (Cancelled).

20. (Currently amended) A method for making a semiconductor chip comprising:
forming a diffusion region in a semiconductor substrate;
forming an insulated trench structure in said substrate which surrounds said diffusion region; and
forming electrical connections on said trench structure and said substrate which receive a control voltage whereby an electric field is produced to control a current flowing ~~is in~~ said diffusion region.
21. (Currently Amended) The method for making a semiconductor chip according to claim 20, further comprising source and drain regions formed in said diffusion on each side of ~~said a~~ gate.
22. (Original) The method of making a semiconductor chip according to claim 20, wherein said diffusion region forms a resistor which has a resistance controlled in response to said control voltage.
23. (Currently Amended) The method of making a semiconductor chip according to claim 20, wherein ~~said diffusion layer region~~ is formed in a well of polysilicon deposited ~~is in~~ said trench structure.
24. (Original) A method for making a semiconductor chip comprising:
forming first and second diffusion regions in a semiconductor substrate;

forming a trench structure around said first and second diffusion regions; and forming a contact on said trench structure and said substrate for controlling current through said diffusion regions.

25. (Original) The method for making a semiconductor chip according to claim 24, further comprising:

forming first and second gates over said first and second diffusion regions.

26. (Currently Amended) A method for making a semiconductor chip comprising:

forming multiple diffusion regions that are surrounded by multiple trench structures on a substrate;

~~forming multiple diffusion regions in said trench structures in said substrate;~~
and

forming multiple contacts on each of said trench structures and said substrate for controlling current through said diffusion regions.

27. (Original) The method for making a semiconductor chip according to claim 26, further comprising:

forming a gate electrode over each of said diffusion regions; and

forming drain and source connections on opposite sides of said gate electrodes.